Ordering number: EN3134

PNP Epitaxial Planar Silicon Transistor



2SA1730

# **High-Speed Switching Applications**

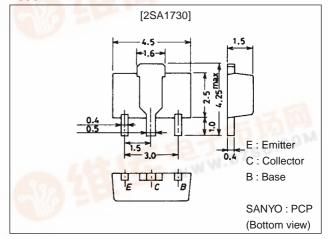
### **Features**

- $\cdot$  Adoption of FBET , MBIT processes.
- · Large current capacity.
- · Low collector-to-emitter saturation voltage.
- · Fast switching speed.
- · Small-sized package.

## **Package Dimensions**

unit:mm

2038



# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		-50	V
Collector-to-Emitter Voltage	VCEO		-40	V
Emitter-to-Base Voltage	V <sub>EBO</sub>	pal.	-5	V
Collector Current	IC	The same of the sa	-3	Α
Collector Current (Pulse)	I <sub>CP</sub>	- s.b. (200 t	-6	Α
Collector Dissipation	PC	Mounted on ceramic board (250mm <sup>2</sup> ×0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	LIMI WILLIAM	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0			-1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V, I <sub>C</sub> =0			1	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA	70*		280*	177
	h <sub>FE</sub> 2	V <sub>CE</sub> =-2V, I <sub>C</sub> =-3A	25			101
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA		300		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz	W.W.	35		pF
Collector-to-Emitter Saturatin Voltage	VCE(sat)	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-75mA		-0.3	-0.8	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-75mA		-0.95	-1.3	V

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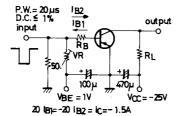
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =-10μA, I <sub>E</sub> =0	-50			V
Collector-to-Emitter Saturation Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =-1mA, R <sub>BE</sub> =∞	-40			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			V
Turn-ON Time	ton	See specified Test Circuit		50	100	ns
Storage Time	t <sub>stg</sub>	See specified Test Circuit		120	220	ns
Turn-OFF Time	toff	See specified Test Circuit		150	300	ns

 $<sup>\</sup>ast$  : The 2SA1730 is classified by 500mA  $h_{FE}$  as follows :

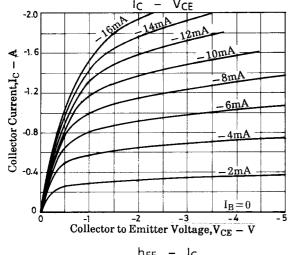
70 Q 140	100 R 200	140 S 280
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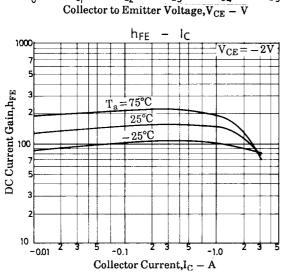
 $\begin{aligned} & Marking: AH \\ & h_{FE} \, rank: Q, \, R, \, S \end{aligned}$ 

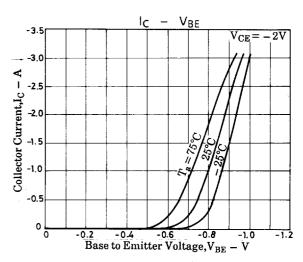
### **Swicthing Time Test Circuit**

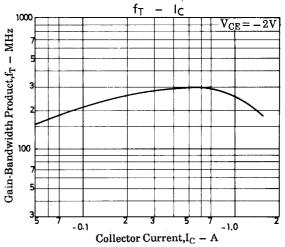


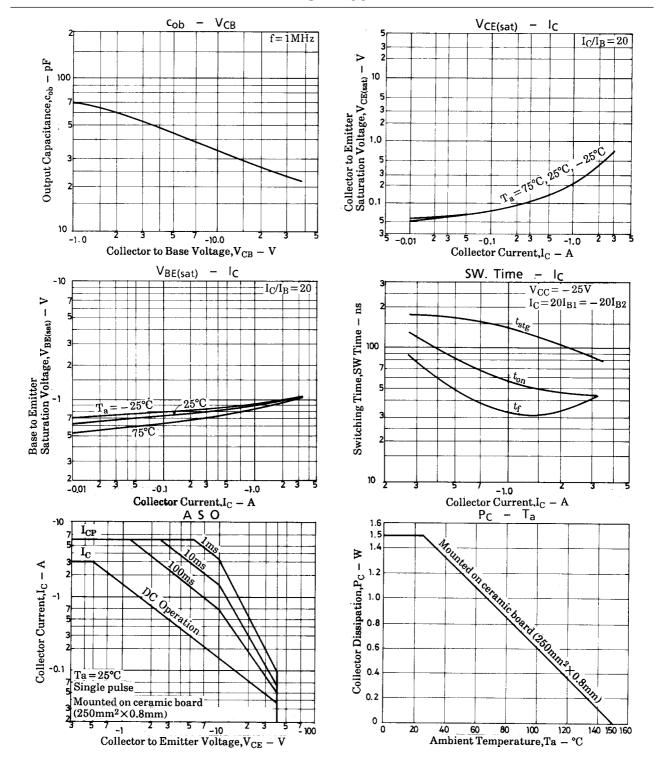
Unit (resistance :  $\Omega$ , capacitance : F)











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